Refine Search

Search Results -

Terms	Documents
5192702	47

Database:
US Pre-Grant Publication Full-Text Database
US Patents Full-Text Database
US OCR Full-Text Database
EPO Abstracts Database
JPO Abstracts Database
Derwent World Patents Index
IBM Technical Disclosure Bulletins

Search: L45

Refine Search

Recall Text Clear Interrupt

Search History

DATE: Wednesday, October 27, 2004 Printable Copy Create Case

Set Name side by side	Query	Hit Count	Set Name result set
DB=USPT; PLUR=YES; OP=OR			
L45	5192702	47	L45
L44	6380583	3	L44
DB=TDBD; PLUR=YES; OP=OR			
L43	L42	0	L43
DB=DWPI; PLUR=YES; OP=OR			
L42	L41	0	L42
DB=JPAB; PLUR=YES; OP=OR			
L41	L40	0	L41
DB=EPAB; PLUR=YES; OP=OR			
L40	L39	0	L40
DB=USOC; PLUR=YES; OP=OR			
L39	L38	0	L39
DB=PGPB; PLUR=YES; OP=OR			
L38	L37	0	L38

h e b b cg b e e ch

DB=USPT; PLUR=YES; OP=OR

L37	L28 and "floating gate"	2	L37
L36	L28 and "split gate"	2	L36

DB=TDBD; PLUR=YES; OP=OR

L35	L34	0	L35
L34	L33	0	L34

DB=DWPI; PLUR=YES; OP=OR

L33	L32	0	L33

DB=JPAB; PLUR=YES; OP=OR

L32	L31	0	L32

DB=EPAB; PLUR=YES; OP=OR

L31	L30	0	L31

DB=USOC; PLUR=YES; OP=OR

L30	L29	0	L30

DB=PGPB; PLUR=YES; OP=OR

L29	L28	0	L29

DB=USPT; PLUR=YES; OP=OR

L28	L27 and (polysilicon near7 ammonia)	3	L28
L27	L26 same ((polysilicon) near7 (etch$5 or remov$5))	61	L27
L26	(oxidized near5 polysilicon) near10 mask	132	L26

DB=DWPI; PLUR=YES; OP=OR

L25	L24	0	L25
L24	L23	0	L24

DB=JPAB; PLUR=YES; OP=OR

L23	L22	0	L23

DB=EPAB; PLUR=YES; OP=OR

L22	L21	0	L22

DB=USOC; PLUR=YES; OP=OR

L21	L20	0	L21

DB=PGPB; PLUR=YES; OP=OR

L20	L19	0	L20

DB=USPT; PLUR=YES; OP=OR

L19	L18 and (oxidized near10 mask)	0	L19
L18	L17 and ((etch$5 or remov$5) near6 polysilicon)	8	L18
L17	L16 and (oxid$5 near6 polysilicon)	10	L17
L16	L15 same (polysilicon near6 ammonia)	14	L16
L15	polysilicon near6 (substrate)	14123	L15
L14	L13 and ((remov$6 or etch$5) near10 poliilicon)	0	L14
L13	L12 and (oxid$6 near7 polysilicon)	6	L13
L12	L11 same (polysilicon near5 ammonia)	10	L12
L11	polysilicon near10 substrate	17242	L11

h e b b cg b e e ch

L10	L8 and (etch$6 near10 (exposed near5 polysilicon))	20	L10
L9	L8 and (etch$6 near10 polysilicon)	74	L9
L8	L5 and (polysilicon near15 oxid$5)	97	L8
L7	L6 and (etch$6 near10 polysilicon)	20	L7
L6	L5 and (photoresist near7 polysilicon)	20	L6
L5	L1 and (polysilicon near15 ammonia)	111	L5
L4	L1 and (polysilicon same amonia)	1	L4
L3	L1 and (polysilicon near15 amonia)	0	L3
L2	L1 and (polysilicon near7 amonia)	0	L2
L1	substrate near6 polysilicon	14123	L1

END OF SEARCH HISTORY

h e b b cg b e e ch